IN THE CLAIMS:

- 1.-2. (Canceled)
- (Currently amended) A driving method of a MOS sensor having a plurality of 3. pixels in an image pick up unit, each of said pixels comprising:
 - a reset transistor;
- a photoelectric conversion element having a first terminal connected to one of source or drain terminals of said reset transistor, and a second terminal connected to a photoelectric conversion element side power source line;
 - a reset signal line connected to a gate terminal of said reset transistor;
- a signal amplifier circuit having an input terminal connected to said one of the source or drain terminals of said reset transistor;
- a reset side power source line connected to other one of the source or drain terminals of said reset transistor;

said method comprising the steps of:

imaging a first object on trial, comprising the steps of:

resetting said plurality of pixels at a same time; and

sequentially selecting at least a part of said plurality of pixels to output signals of the selected pixels;

determining a storage period in accordance with a period from the time of said resetting to a time when the signal of the selected pixels saturate; and

imaging a second object in the storage period

imaging a second object ordinarily, comprising the steps of:

resetting said plurality of pixels sequentially; and

selecting said plurality of pixels sequentially after said storage period has passed since resetting said plurality of pixels.

- (Currently amended) A driving method of a MOS sensor having a plurality of 4. pixels in an image pick up unit, each of said pixels comprising:
 - a reset transistor;
 - a photoelectric conversion element having a first terminal connected to one of source

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or drain terminals of said reset transistor, and a second terminal connected to a photoelectric conversion element side power source line;

a reset signal line connected to a gate terminal of said reset transistor;

a signal amplifier circuit having an input terminal connected to said one of the source or drain terminals of said reset transistor;

a reset side power source line connected to other one of the source or drain terminals of said reset transistor,

said method comprising the steps of:

imaging a first object on trial, comprising the steps of:

resetting said plurality of pixels at a same time; and

sequentially selecting a [[par]] part of the plurality of pixels to output signals of the selected pixels;

determining a storage period in accordance with a period from the time of said resetting to a time when one of the signals of the selected pixels saturates; and

imaging a second object in the storage period

imaging a second object ordinarily, comprising the steps of:

resetting said plurality of pixels sequentially; and

selecting said plurality of pixels sequentially after said storage period has passed since resetting said plurality of pixels;

wherein said one of the signals has a largest signal amplitude among the signals of the selected pixels.

(Currently amended) A driving method of a MOS sensor having a plurality of 5. pixels in an image pick up unit, each of said pixels comprising:

a reset transistor;

a photoelectric conversion element having a first terminal connected to one of source or drain terminals of said reset transistor, and a second terminal connected to a photoelectric conversion element side power source line;

a reset signal line connected to a gate terminal of said reset transistor;

a signal amplifier circuit having an input terminal connected to said one of the source or drain terminals of said reset transistor;

a reset side power source line connected to other one of the source or drain terminals of said reset transistor;

said method comprising the steps of:

imaging a first object on trial, comprising the steps of:

resetting said plurality of pixels at a same time; and

sequentially selecting the plurality of pixels to output signals of the selected pixels;

determining a storage period in accordance with a period from the time of said resetting to a time when the photoelectric conversion element(s) of the selected pixels saturates; and

imaging a second-object in the storage period

imaging a second object ordinarily, comprising the steps of:

resetting said plurality of pixels sequentially; and

selecting said plurality of pixels sequentially after said storage period has passed since resetting said plurality of pixels.

- (Currently amended) A driving method of a MOS sensor having a plurality of 6. pixels in an image pick up unit, each of said pixels comprising:
 - a reset transistor;
- a photoelectric conversion element having a first terminal connected to one of source or drain terminals of said reset transistor, and a second terminal connected to a photoelectric conversion element side power source line;
 - a reset signal line connected to a gate terminal of said reset transistor;
- a signal amplifier circuit having an input terminal connected to said one of the source or drain terminals of said reset transistor;
- a reset side power source line connected to other one of the source or drain terminals of said reset transistor;

said method comprising the steps of:

imaging a first object on trial, comprising the steps of:

resetting a part of said plurality of pixels at a same time; and sequentially selecting the plurality of pixels to output signals of the selected pixels;

determining a storage period in accordance with a period from the time of said resetting to a time when any one of the photoelectric conversion elements of the selected pixels saturates; and

imaging a second object in the storage period

imaging a second object ordinarily, comprising the steps of:

resetting said plurality of pixels sequentially; and

selecting said plurality of pixels sequentially after said storage period has passed since resetting said plurality of pixels.

- 7. (Original) The method according to claim 3 wherein a value of said storage period is set by irradiating said image pick up unit with light having a highest intensity among lights which have been reflected by an object to enter said image pick up unit.
- 8. (Original) The method according to claim 4 wherein a value of said storage period is set by irradiating said image pick up unit with light having a highest intensity among lights which have been reflected by an object to enter said image pick up unit.
- 9. (Original) The method according to claim 5 wherein a value of said storage period is set by irradiating said image pick up unit with light having a highest intensity among lights which have been reflected by an object to enter said image pick up unit.
- 10. (Original) The method according to claim 6 wherein a value of said storage period is set by irradiating said image pick up unit with light having a highest intensity among lights which have been reflected by an object to enter said image pick up unit.
- 11. (Original) The method according to claim 3 wherein the signals are outputted exclusively from those of the plurality of pixels of said image pick up unit that belong to a limited area.

- 12. (Original) The method according to claim 4 wherein the signals are outputted exclusively from those of the plurality of pixels of said image pick up unit that belong to a limited area.
- 13. (Original) The method according to claim 5 wherein the signals are outputted exclusively from those of the plurality of pixels of said image pick up unit that belong to a limited area.
- 14. (Original) The method according to claim 6 wherein the signals are outputted exclusively from those of the plurality of pixels of said image pick up unit that belong to a limited area.
- 15. (Original) The method according to claim 3 wherein the image of an object is picked up by using said storage period.
- 16. (Original) The method according to claim 4 wherein the image of an object is picked up by using said storage period.
- 17. (Original) The method according to claim 5 wherein the image of an object is picked up by using said storage period.
- 18. (Original) The method according to claim 6 wherein the image of an object is picked up by using said storage period.

19.- 20. (Canceled)

21. (Currently amended) A MOS sensor comprising a plurality of pixels in an image pickup unit,

wherein said pixel includes a photoelectric conversion element, a resetting transistor and a signal amplifier circuit,

wherein said photoelectric conversion element is connected at its one terminal with

the source terminal or drain terminal of said resetting transistor and at its other terminal with a photoelectric conversion element side power line,

wherein said resetting transistor is connected at its gate terminal with a reset signal line, and

wherein said resetting transistor is connected at its source terminal or drain terminal with said photoelectric conversion element and the input terminal of said signal amplifier circuit and at its other with a reset side power line,

whereby, in a trial imaging period, a plurality of first pixels of said image pickup unit are sequentially selected, after all the plurality of the pixels reset simultaneously, so that the signals of the selected pixels are outputted, and

whereby the period from said reset time to the time when the signals of said selected pixels are saturated is set to the value of a storage period and

whereby, in the storage period, a plurality of second pixels of said image pickup unit are selected in an ordinary imaging period, a plurality of second pixels of said image pickup unit are selected sequentially, after said storage period has passed since said plurality of second pixels were reset sequentially.

22. (Currently amended) A MOS sensor comprising a plurality of pixels in an image pickup unit,

wherein said pixel includes a photoelectric conversion element, a resetting transistor and a signal amplifier circuit,

wherein said photoelectric conversion element is connected at its one terminal with the source terminal or drain terminal of said resetting transistor and at its other terminal with a photoelectric conversion element side power line,

wherein said resetting transistor is connected at its gate terminal with a reset signal line, and

wherein said resetting transistor is connected at its source terminal or drain terminal with said photoelectric conversion element and the input terminal of said signal amplifier circuit and at its other with a reset side power line,

whereby, in a trial imaging period, a plurality of first pixels of said image pickup unit are sequentially selected, after all reset simultaneously, so that the signals of the selected

pixels are outputted, and

whereby the period from said reset time to the time when the signal having the largest amplitude of said selected pixels is saturated is set to the value of a storage period, and

whereby, in the storage period, a plurality of second pixels of said image pickup unit are selected in an ordinary imaging period, a plurality of second pixels of said image pickup unit are selected sequentially, after said storage period has passed since said plurality of second pixels were reset sequentially.

23. (Currently amended) A MOS sensor comprising a plurality of pixels in an image pickup unit,

wherein said pixel includes a photoelectric conversion element, a resetting transistor and a signal amplifier circuit,

wherein said photoelectric conversion element is connected at its one terminal with the source terminal or drain terminal of said resetting transistor and at its other terminal with a photoelectric conversion element side power line,

wherein said resetting transistor is connected at its gate terminal with a reset signal line, and

wherein said resetting transistor is connected at its source terminal or drain terminal with said photoelectric conversion element and the input terminal of said signal amplifier circuit and at its other with a reset side power line,

whereby, in a trial imaging period, a plurality of first pixels of said image pickup unit are sequentially selected, after all the plurality of the pixels reset simultaneously, so that the signals of the selected pixels are outputted, and

whereby the period from said reset time to the time when the photoelectric conversion elements of said selected pixels are saturated is set to the value of a storage period, and

whereby, in the storage period, a plurality of second pixels of said image pickup unit are selected in an ordinary imaging period, a plurality of second pixels of said image pickup unit are selected sequentially, after said storage period has passed since said plurality of second pixels were reset sequentially.

24. (Currently amended) A MOS sensor comprising a plurality of pixels in an w7014042

image pickup unit,

wherein said pixel includes a photoelectric conversion element, a resetting transistor and a signal amplifier circuit,

wherein said photoelectric conversion element is connected at its one terminal with the source terminal or drain terminal of said resetting transistor and at its other terminal with a photoelectric conversion element side power line,

wherein said resetting transistor is connected at its gate terminal with a reset signal line, and

wherein said resetting transistor is connected at its source terminal or drain terminal with said photoelectric conversion element and the input terminal of said signal amplifier circuit and at its other with a reset side power line,

whereby, in a trial imaging period, a plurality of first pixels of said image pickup unit are sequentially selected, after all reset simultaneously, so that the signals of the selected pixels are outputted, and

whereby the period from said reset time to the time when any one of the photoelectric conversion elements of said selected pixels is saturated is set to the value of a storage period, and

whereby, in the sterage period, a plurality of second pixels of said image pickup unit are selected in an ordinary imaging period, a plurality of second pixels of said image pickup unit are selected sequentially, after said storage period has passed since said plurality of second pixels were reset sequentially.

- (Original) A MOS sensor according to claim 21 wherein the value of said 25. storage period is set by irradiating said image pickup unit with that of the highest intensity of the lights which have been reflected by an object to enter said image pickup unit.
- (Original) A MOS sensor according to claim 22 wherein the value of said 26. storage period is set by irradiating said image pickup unit with that of the highest intensity of the lights which have been reflected by an object to enter said image pickup unit.
- (Original) A MOS sensor according to claim 23 wherein the value of said 27. W701404.2

storage period is set by irradiating said image pickup unit with that of the highest intensity of the lights which have been reflected by an object to enter said image pickup unit.

- 28. (Original) A MOS sensor according to claim 24 wherein the value of said storage period is set by irradiating said image pickup unit with that of the highest intensity of the lights which have been reflected by an object to enter said image pickup unit.
- 29. (Original) A MOS sensor according to claim 23 wherein the signals are outputted exclusively from those of the plurality of pixels of said image pickup unit that belong to a limited area.
- 30. (Original) A MOS sensor according to claim 24 wherein the signals are outputted exclusively from those of the plurality of pixels of said image pickup unit that belong to a limited area.
- 31. (Original) A MOS sensor according to claim 25 wherein the signals are outputted exclusively from those of the plurality of pixels of said image pickup unit that belong to a limited area.
- 32. (Original) A MOS sensor according to claim 26 wherein the signals are outputted exclusively from those of the plurality of pixels of said image pickup unit that belong to a limited area.
- 33. (Original) A MOS sensor according to claim 23 wherein the image of an object is picked up by using said storage period.
- 34. (Original) A MOS sensor according to 24 wherein the image of an object is picked up by using said storage period.
- 35. (Original) A MOS sensor according to claim 25 wherein the image of an object is picked up by using said storage period.

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- 36. (Original) A MOS sensor according to claim 26 wherein the image of an object is picked up by using said storage period.
 - 37. (Canceled)
 - 38. (Original) A scanner using said MOS sensor according to claim 3.
 - 39. (Original) A scanner using said MOS sensor according to claim 4.
 - 40. (Original) A scanner using said MOS sensor according to claim 5.
 - 41. (Original) A scanner using said MOS sensor according to claim 6.
 - 42. (Original) A scanner using said MOS sensor according to claim 10.
 - 43. (Original) A scanner using said MOS sensor according to claim 12.
 - 44. (Original) A scanner using said MOS sensor according to claim 13.
 - 45. (Original) A scanner using said MOS sensor according to claim 14.
 - 46. (Original) A scanner using said MOS sensor according to claim 15.
 - 47. (Canceled)
 - 48. (Original) A mobile information terminal using said MOS sensor according to claim 3.
 - 49. (Original) A mobile information terminal using said MOS sensor according to claim 4.

- 50. (Original) A mobile information terminal using said MOS sensor according to claim 5.
- 51. (Original) A mobile information terminal using said MOS sensor according to claim 6.
- 52. (Original) A mobile information terminal using said MOS sensor according to claim 10.
- 53. (Original) A mobile information terminal using said MOS sensor according to claim 12.
- 54. (Original) A mobile information terminal using said MOS sensor according to claim 13.
- 55. (Original) A mobile information terminal using said MOS sensor according to claim 14.
- 56. (Original) A mobile information terminal using said MOS sensor according to claim 15.
 - 57. (Canceled)
- 58. (Original) A fingerprint reading device using said MOS sensor according to claim 3.
- 59. (Original) A fingerprint reading device using said MOS sensor according to claim 4.
- 60. (Original) A fingerprint reading device using said MOS sensor according to claim 5.

- 61. (Original) A fingerprint reading device using said MOS sensor according to claim 6.
- 62. (Original) A fingerprint reading device using said MOS sensor according to claim 10.
- 63. (Original) A fingerprint reading device using said MOS sensor according to claim 12.
- 64. (Original) A fingerprint reading device using said MOS sensor according to claim 13
- 65. (Original) A fingerprint reading device using said MOS sensor according to claim 14.
- 66. (Original) A fingerprint reading device using said MOS sensor according to claim 15.
 - 67. (Canceled)
- 68. (Original) An electric apparatus having said MOS sensor according to claim 3 wherein said electronic apparatus is selected from the group consisting of a digital still camera, a mobile phone, a mobile game device, and a personal computer.
- 69. (Original) An electric apparatus having said MOS sensor according to claim 4 wherein said electronic apparatus is selected from the group consisting of a digital still camera, a mobile phone, a mobile game device, and a personal computer.
- 70. (Original) An electric apparatus having said MOS sensor according to claim 5 wherein said electronic apparatus is selected from the group consisting of a digital still w7014042

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camera, a mobile phone, a mobile game device, and a personal computer.

- 71. (Original) An electric apparatus having said MOS sensor according to claim 6 wherein said electronic apparatus is selected from the group consisting of a digital still camera, a mobile phone, a mobile game device, and a personal computer.
- 72. (Original) An electric apparatus having said MOS sensor according to claim 10 wherein said electronic apparatus is selected from the group consisting of a digital still camera, a mobile phone, a mobile game device, and a personal computer.
- 73. (Original) An electric apparatus having said MOS sensor according to claim 12 wherein said electronic apparatus is selected from the group consisting of a digital still camera, a mobile phone, a mobile game device, and a personal computer.
- 74. (Original) An electric apparatus having said MOS sensor according to claim 13 wherein said electronic apparatus is selected from the group consisting of a digital still camera, a mobile phone, a mobile game device, and a personal computer.
- 75. (Original) An electric apparatus having said MOS sensor according to claim 14 wherein said electronic apparatus is selected from the group consisting of a digital still camera, a mobile phone, a mobile game device, and a personal computer.
- 76. (Original) An electric apparatus having said MOS sensor according to claim 15 wherein said electronic apparatus is selected from the group consisting of a digital still camera, a mobile phone, a mobile game device, and a personal computer.

77. (Canceled)

78. (Previously Presented) The method according to claim 3 wherein the first object is second object.

- (Previously Presented) The method according to claim 4 wherein the first 79. object is second object.
- (Previously Presented) The method according to claim 5 wherein the first 80. object is second object.
- (Previously Presented) The method according to claim 6 wherein the first 81. object is second object.
 - (Canceled) 82.
- (Previously Presented) The MOS sensor according to claim 21 wherein the 83. plurality of first pixels are the plurality of second pixels.
- (Previously Presented) The MOS sensor according to claim 22 wherein the 84. plurality of first pixels are the plurality of second pixels.
- (Previously Presented) The MOS sensor according to claim 23 wherein the 85. plurality of first pixels are the plurality of second pixels.
- (Previously Presented) The MOS sensor according to claim 24 wherein the 86. plurality of first pixels are the plurality of second pixels.
 - (Canceled) 87.
- (Currently amended) A driving method of a MOS sensor having a plurality of 88. pixels in an image pick up unit, each of said pixels comprising:
 - a reset transistor:
- a photoelectric conversion element having a first terminal connected to one of source or drain terminals of said reset transistor, and a second terminal connected to a photoelectric conversion element side power source line;
 - a reset signal line connected to a gate terminal of said reset transistor;

a signal amplifier circuit having an input terminal connected to said one of the source or drain terminals of said reset transistor;

a reset side power source line connected to other one of the source or drain terminals of said reset transistor;

said method comprising the steps of:

imaging a first object on trial, comprising the steps of:

resetting said plurality of pixels at a same time; and

sequentially selecting a part of said plurality of pixels to output signals of the selected pixels;

determining a storage period in accordance with a period from the time of said resetting to a time when the signal of the selected pixels saturates; and

imaging a second object in the storage period, comprising the steps of sequentially selecting all of said plurality of pixels to output signals of the selected pixels

imaging a second object ordinarily, comprising the steps of.

resetting said plurality of pixels sequentially; and

selecting said plurality of pixels sequentially after said storage period has passed since resetting said plurality of pixels.